

FQB5N90 / FQI5N90

N-Channel QFET® MOSFET

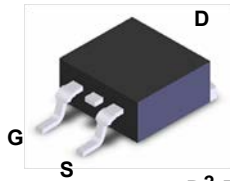
900 V, 5.4 A, 2.3 Ω

Description

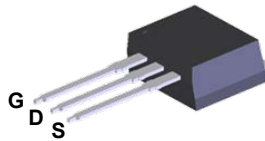
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

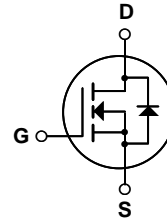
- 5.4 A, 900 V, $R_{DS(on)} = 2.3 \Omega$ (Max.)@ $V_{GS} = 10 V$, $I_D = 2.7 A$
- Low Gate Charge (Typ. 31 nC)
- Low C_{rss} (Typ. 13 pF)
- 100% Avalanche Tested
- RoHS Compliant



D²-PAK



I²-PAK



Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	FQB5N90 / FQI5N90	Unit
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous ($T_C = 25^\circ C$)	5.4	A
	- Continuous ($T_C = 100^\circ C$)	3.42	A
I_{DM}	Drain Current - Pulsed (Note 1)	21.6	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	660	mJ
I_{AR}	Avalanche Current (Note 1)	5.4	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	15.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ C$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ C$)	158	W
	- Derate above $25^\circ C$	1.27	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	FQB5N90 / FQI5N90	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.79	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	40	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ C/W$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	1.0	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$	--	1.8	2.3	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 2.7\text{ A}$ (Note 4)	--	5.6	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1200	1550	pF
C_{oss}	Output Capacitance		--	110	145	pF
C_{rss}	Reverse Transfer Capacitance		--	13	17	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 5.4\text{ A},$ $R_G = 25\ \Omega$	--	28	65	ns
t_r	Turn-On Rise Time		--	65	140	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	140	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	50	110
Q_g	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 5.4\text{ A},$ $V_{GS} = 10\text{ V}$	--	31	40	nC
Q_{gs}	Gate-Source Charge		--	7.2	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	15	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	5.4	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	21.6	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 5.4\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 5.4\text{ A},$	--	610	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	5.26	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 43\text{mH}, I_{AS} = 5.4\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 5.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

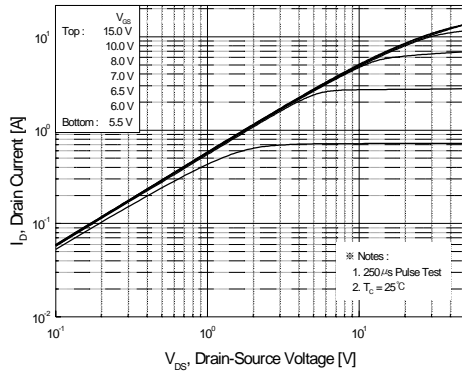


Figure 1. On-Region Characteristics

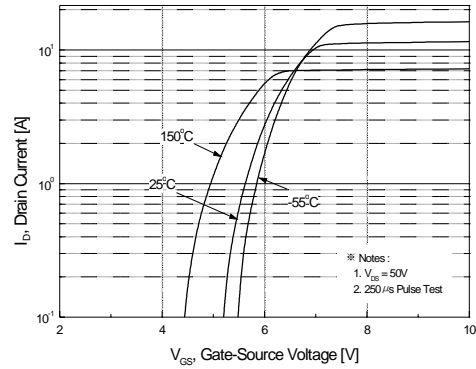


Figure 2. Transfer Characteristics

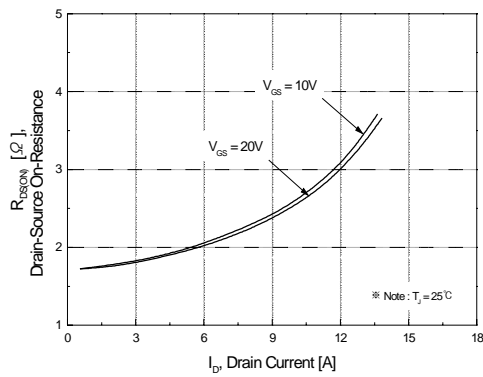


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

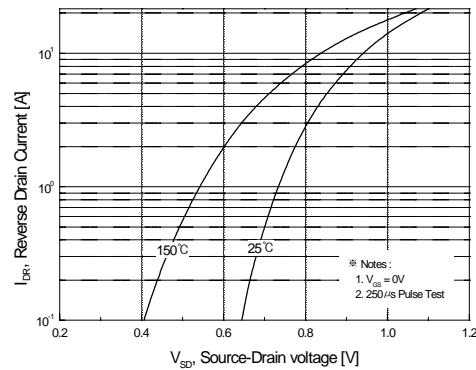


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

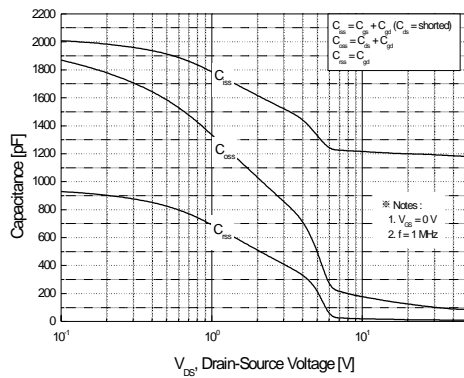


Figure 5. Capacitance Characteristics

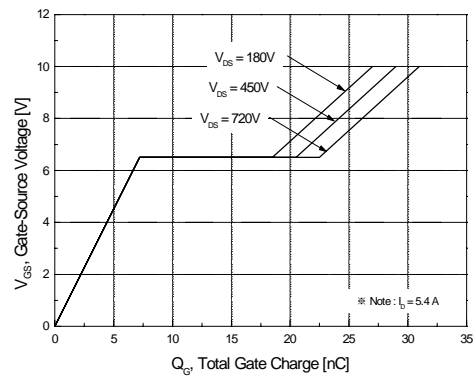


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

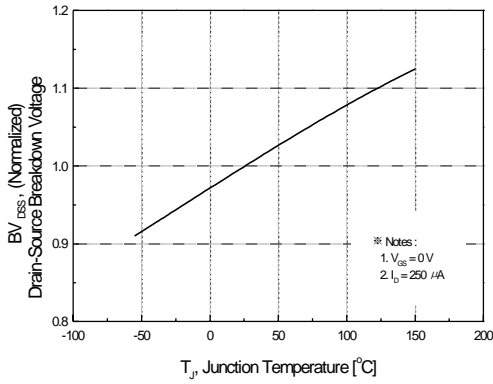


Figure 7. Breakdown Voltage Variation vs. Temperature

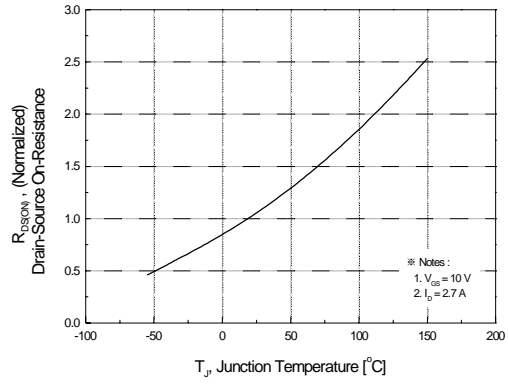


Figure 8. On-Resistance Variation vs. Temperature

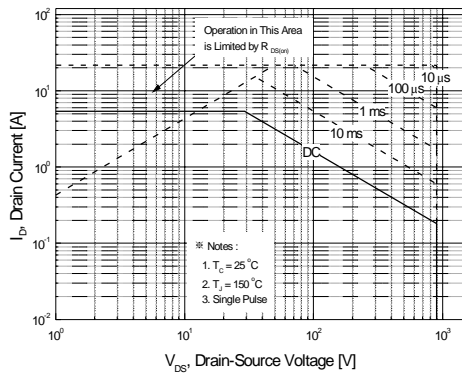


Figure 9. Maximum Safe Operating Area

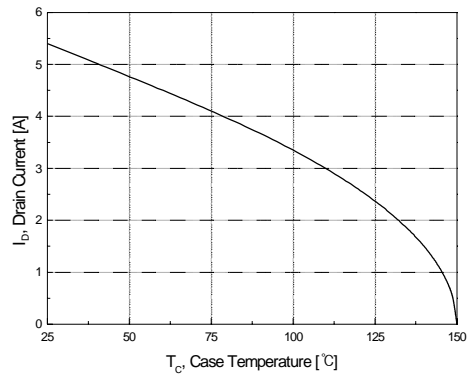


Figure 10. Maximum Drain Current vs. Case Temperature

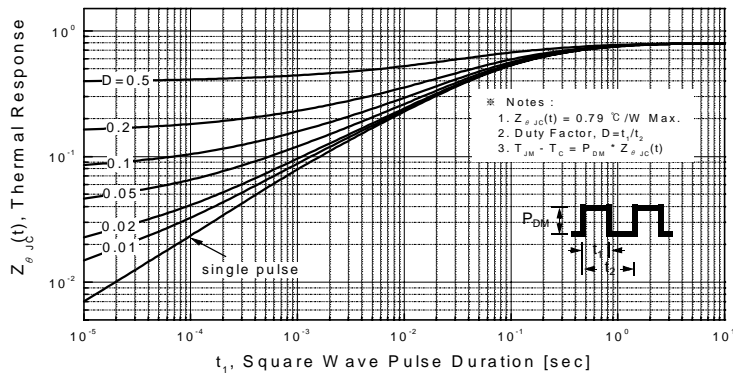
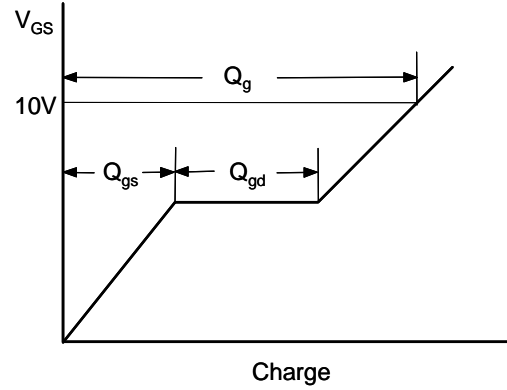
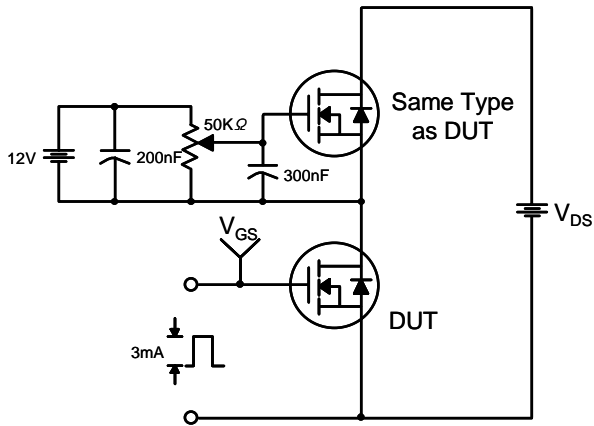
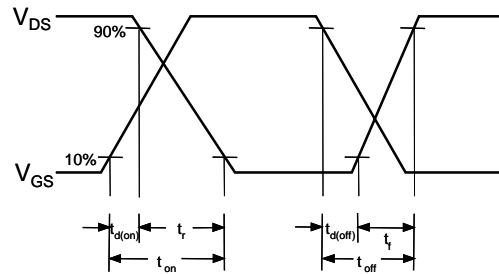
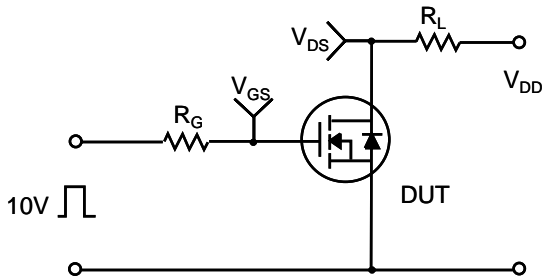


Figure 11. Transient Thermal Response Curve

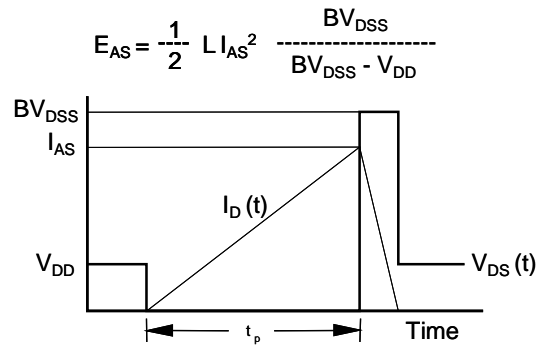
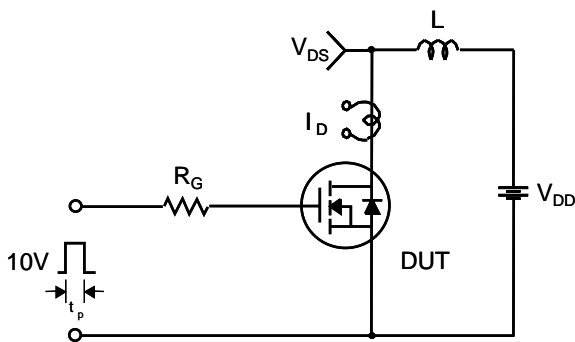
Gate Charge Test Circuit & Waveform



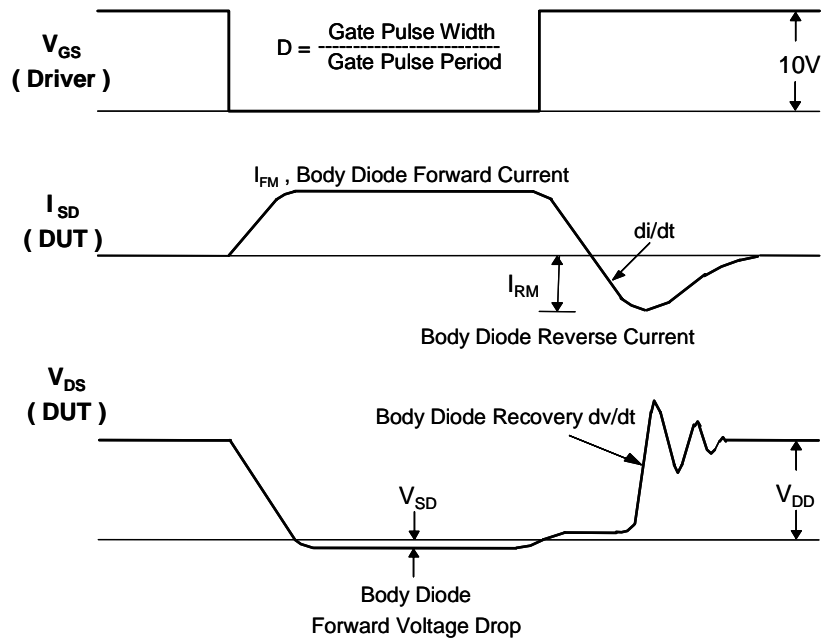
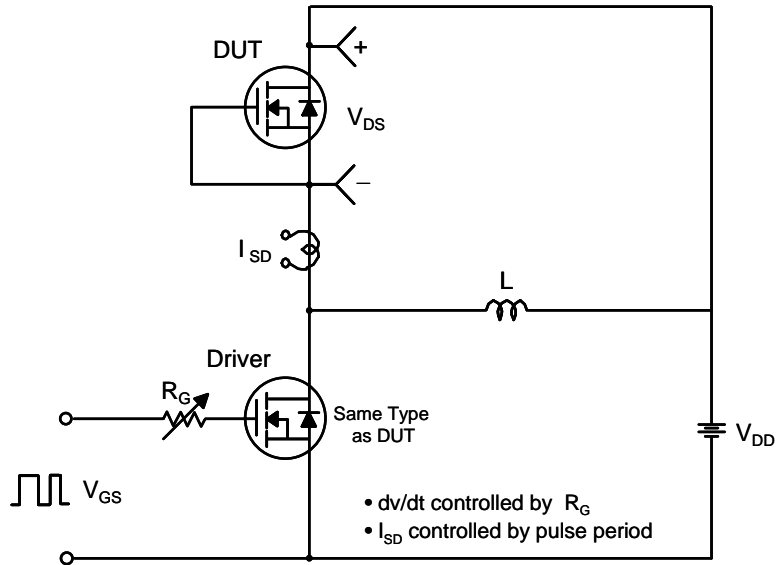
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

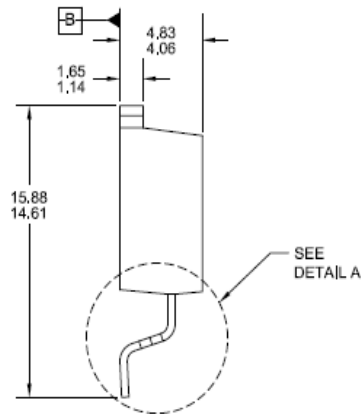
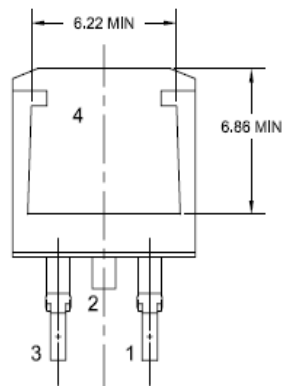
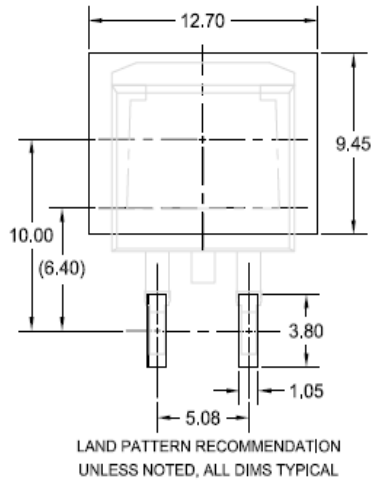
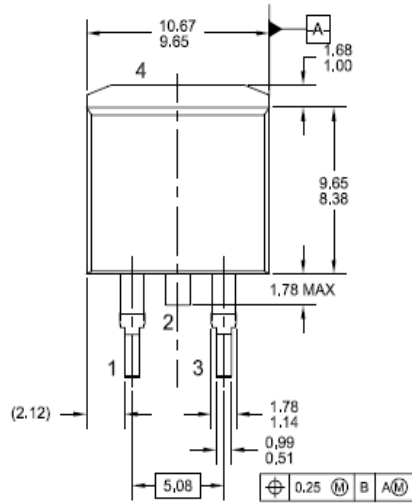


Peak Diode Recovery dv/dt Test Circuit & Waveforms

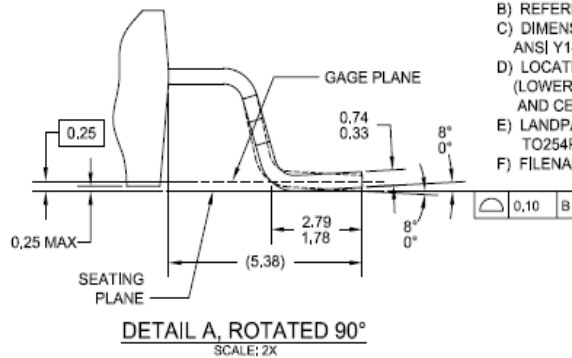


Mechanical Dimensions

D²PAK



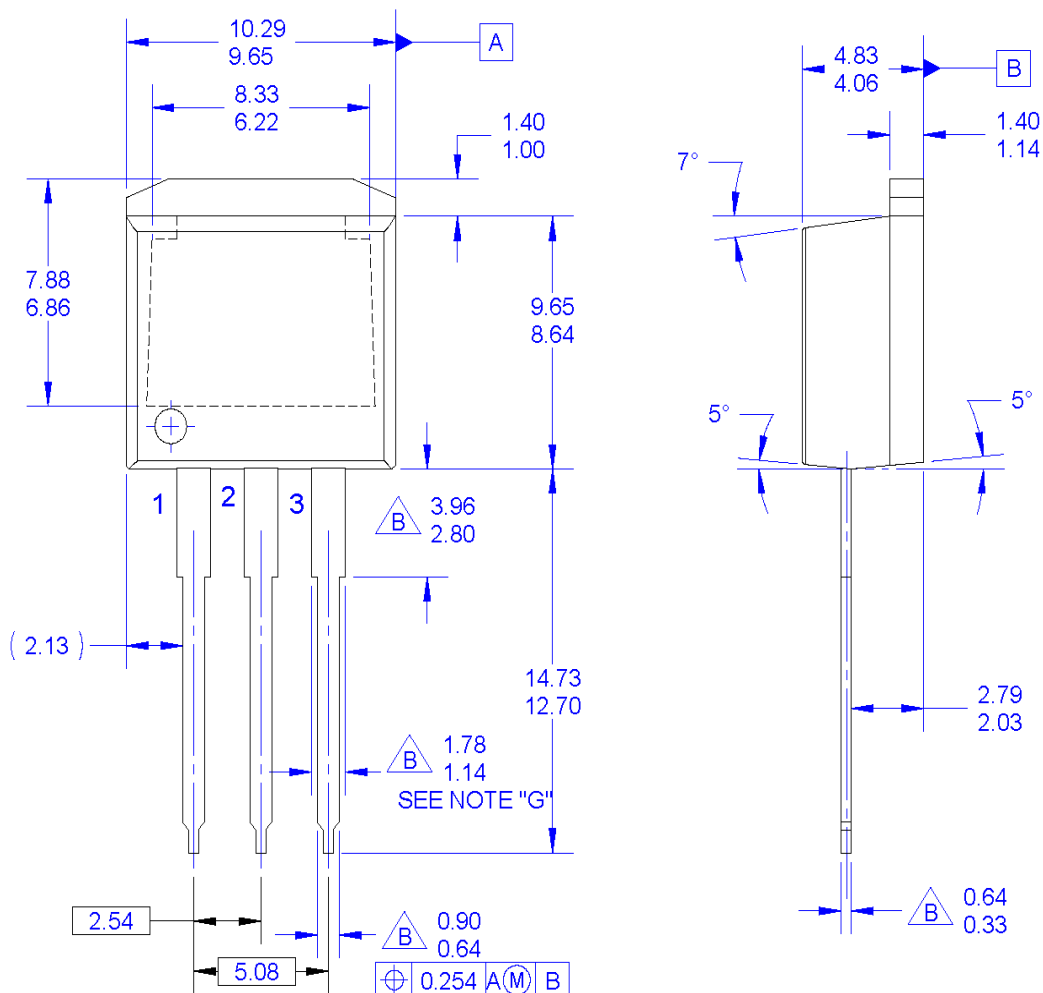
- NOTES: UNLESS OTHERWISE SPECIFIED
 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) REFERENCE JEDEC, TO-263, VARIATION AB.
 C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.
 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
 E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
 F) FILENAME: TO263A02REV6



Dimensions in Millimeters

Mechanical Dimensions

I²PAK



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.
- B. DOES NOT COMPLY JEDEC STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
- G. MAXIMUM WIDTH FOR F-102 DEVICE = 1.35 MAX.
- H. DRAWING FILE NAME: TO262A03REV5

Dimensions in Millimeters



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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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